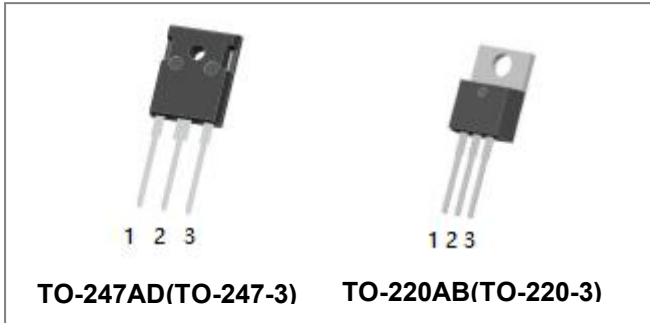


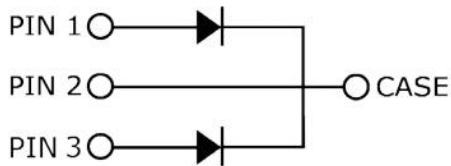
## S3D20065D S3D20065C 650V SiC POWER SCHOTTKY RECTIFIER



### Description

S3D20065D/S3D20065C are SiC Schottky rectifiers packaged in TO-247AD(TO-247-3)/TO-220AB(TO-220-3) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D20065D/S3D20065C are ideal for energy sensitive, high frequency applications in challenging environments.

### Circuit Diagram



### Features

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

### Maximum Ratings(per leg)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_{DC}$	-	650	V
Average Rectified Forward Current	$I_{F(AV)1}$	$T_C=25^{\circ}C$	31	A
	$I_{F(AV)2}$	$T_C=135^{\circ}C$	14	A
	$I_{F(AV)3}$	$T_C=150^{\circ}C$	10	A
Repetitive Peak Forward Surge Current	$I_{FRM1}$	10ms, Half Sine pulse, $T_C=25^{\circ}C$	55	A
	$I_{FRM2}$	10ms, Half Sine pulse, $T_C=110^{\circ}C$	40	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM1}$	10ms, Half Sine pulse, $T_C=25^{\circ}C$	115	A
	$I_{FSM2}$	10ms, Half Sine pulse, $T_C=110^{\circ}C$	80	A
Non-Repetitive Peak Forward Surge Current	$I_{F,Max1}$	10 $\mu$ s. Pulse, $T_C=25^{\circ}C$	995	A
	$I_{F,Max2}$	10 $\mu$ s. Pulse, $T_C=110^{\circ}C$	685	A
Power Dissipation	$P_{tot1}$	$T_C=25^{\circ}C$	103	W
	$P_{tot2}$	$T_C=110^{\circ}C$	45	W
TO-247 Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	bf-in

### Electrical Characteristics(per leg)

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 10A, Pulse, $T_J = 25^{\circ}C$	1.45	1.7	V
	$V_{F2}$	@ 10A, Pulse, $T_J = 175^{\circ}C$	1.65	2.0	V
Reverse Current*	$I_{R1}$	@ $V_R =$ rated $V_R$ , $T_J = 25^{\circ}C$	0.7	40	$\mu$ A
	$I_{R2}$	@ $V_R =$ rated $V_R$ , $T_J = 175^{\circ}C$	7	160	$\mu$ A
Junction Capacitance	$C_T$	$V_R=0V$ , $T_J=25^{\circ}C$ , $f=1MHz$	787	-	pF
Reverse Recovery Charge	$Q_C$	$I_F = 10A$ , $di/dt = 200A/\mu s$ $V_R = 400V$ , $T_J = 25^{\circ}C$	49.1	-	nC
Capacitance Stored Energy	$E_C$	$V_R = 400V$ , $T_J = 25^{\circ}C$	12.03	-	$\mu$ J

\* Pulse width < 300  $\mu$ s, duty cycle < 2%

### Thermal-Mechanical Specifications:

Characteristics	Symbol	S3D20065D	S3D20065C	Units
Junction Temperature	$T_J$	-55 to +175		$^{\circ}C$
Storage Temperature	$T_{stg}$	-55 to +175		$^{\circ}C$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	0.84(per leg) 0.42(both leg)	2.4(per leg) 1.2(both leg)	$^{\circ}C/W$

**Ratings and Characteristics Curves (per leg)**

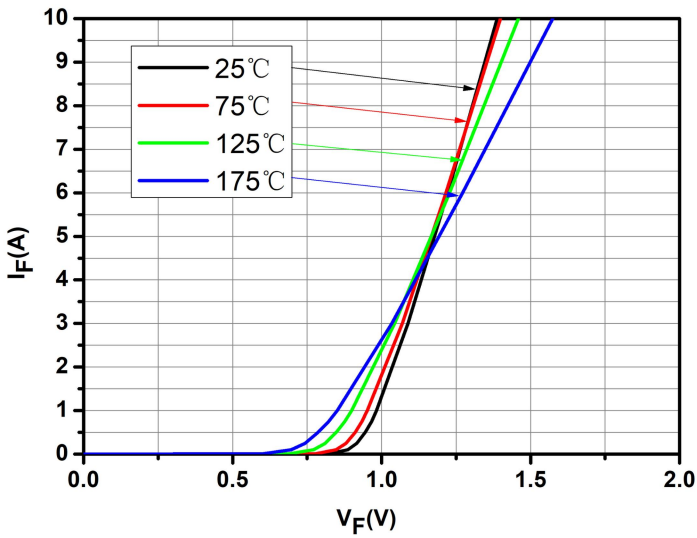


Fig.1-Typical Forward Voltage Characteristics

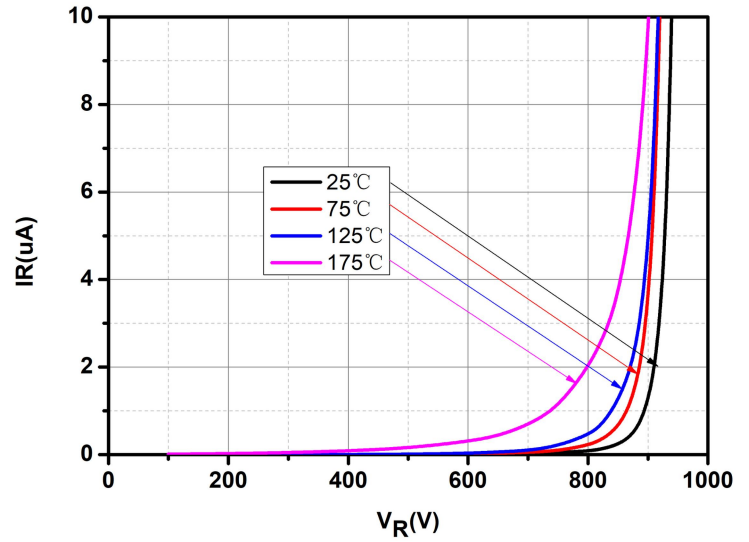


Fig.2-Typical Reverse Characteristics

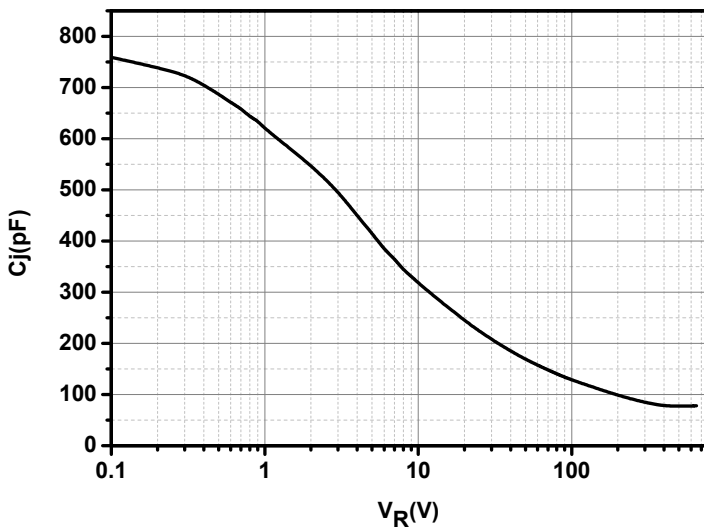


Fig.3-Capacitance vs. Reverse Voltage

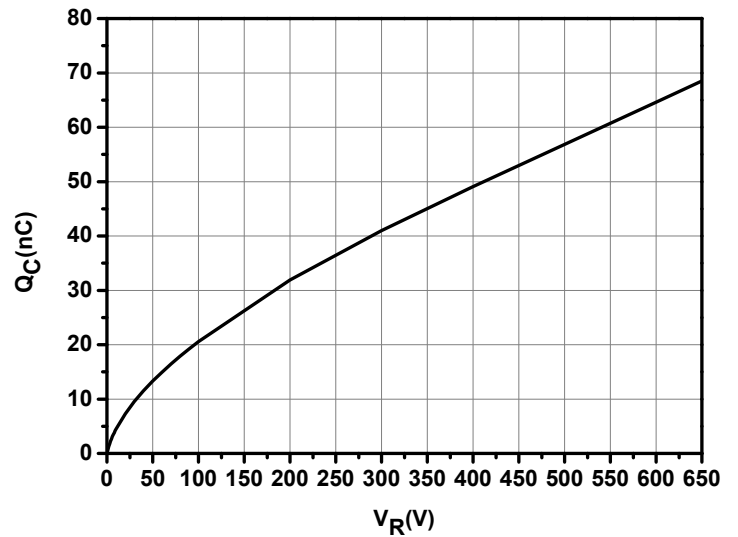


Fig.4-Total Capacitance Charge vs. Reverse Voltage

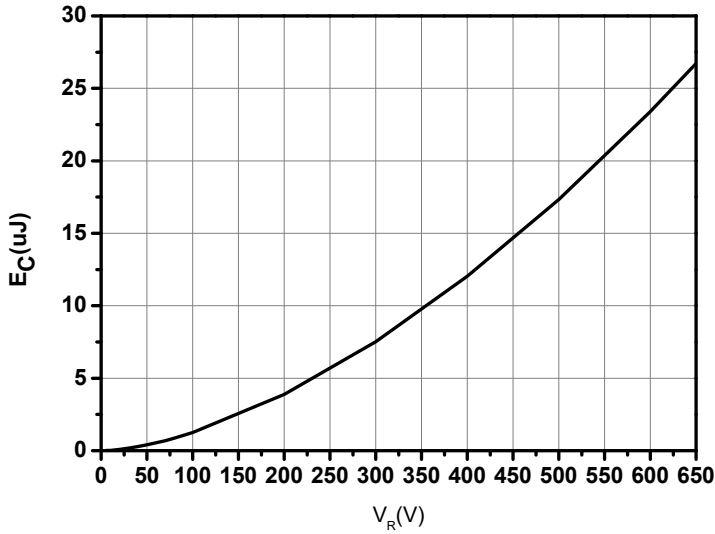


Fig.5-Capacitance Stored Energy

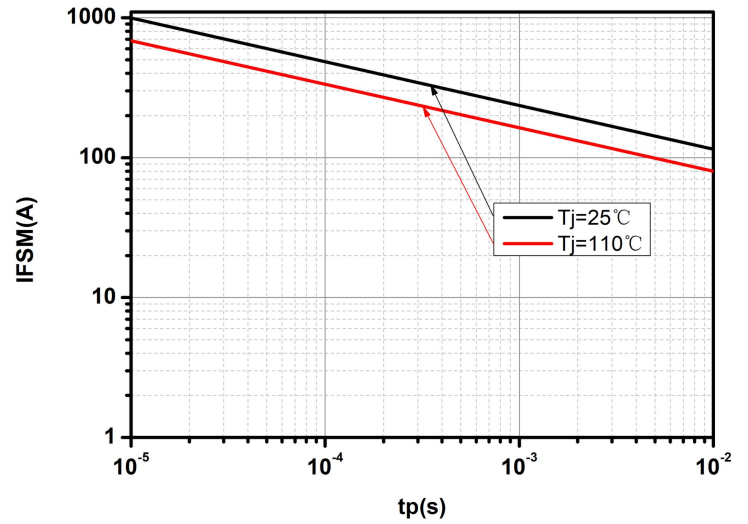


Fig.6-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

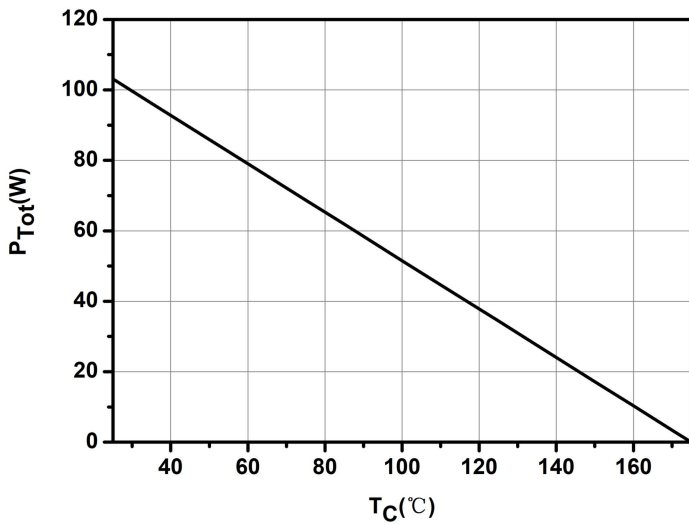


Fig.7-Power Derating

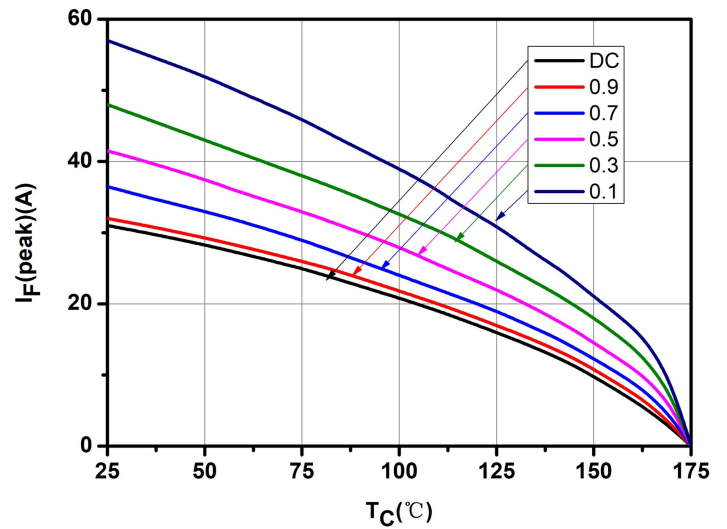
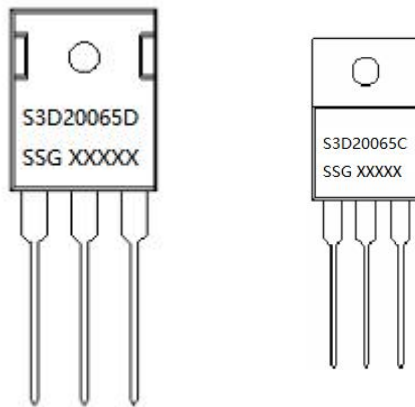


Fig.8-Current Derating

## Ordering Information

Device	Package	Shipping
S3D20065D	TO-247AD(TO-247-3)	25pcs /tube
S3D20065C	TO-220AB(TO-220-3)	50pcs /tube

## Marking Diagram

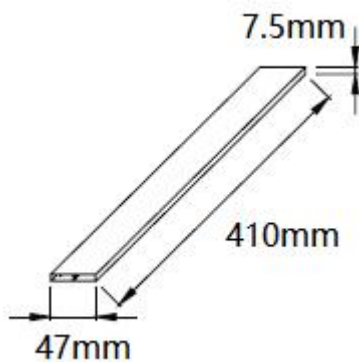


Where XXXXX is YYWWL

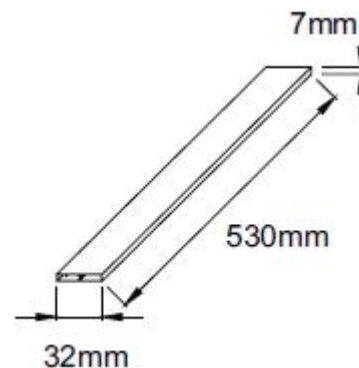
S3D = Device Type  
D/C = Package type  
20 = Forward Current (20A)  
065 = Reverse Voltage (650V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

## Tube Specification

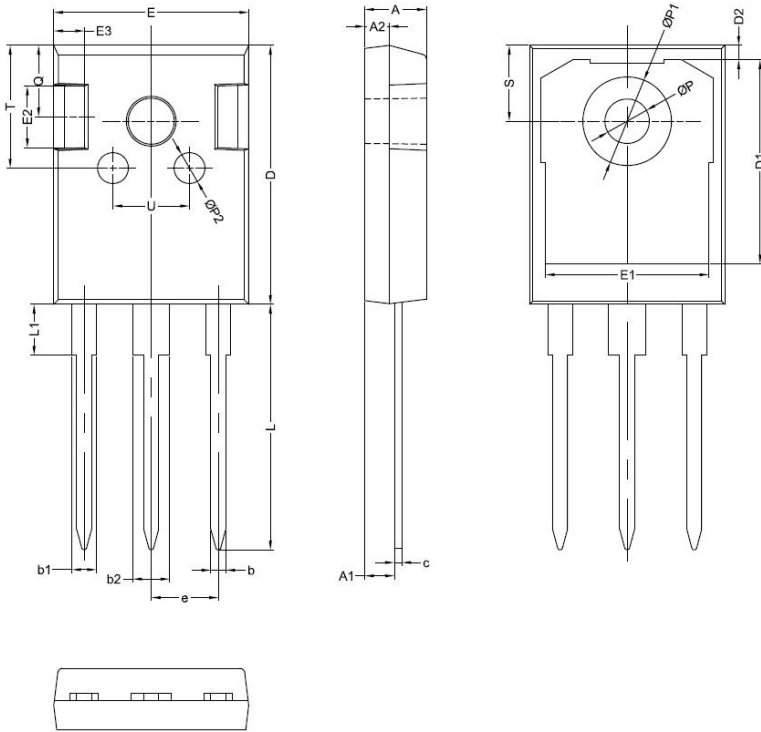


TO-247AD(TO-247-3)



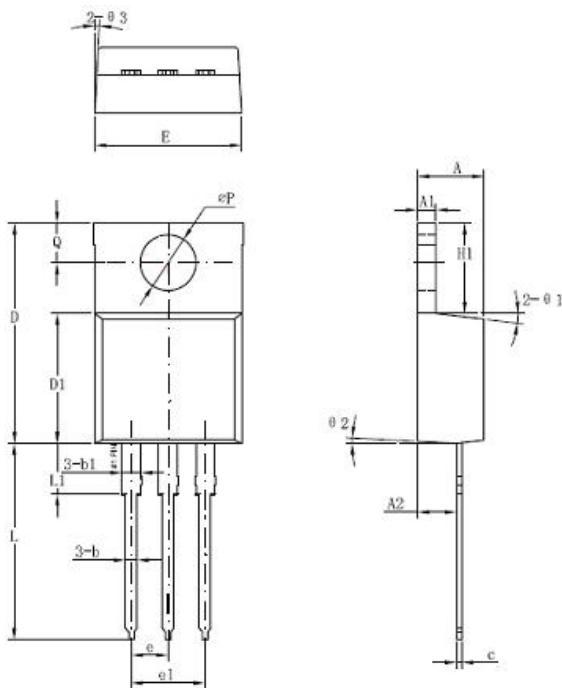
TO-220AB(TO-220-3)

**Mechanical Dimensions TO-247AD**



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80		5.20
A1	2.00		2.75
A2	1.90		2.10
b	1.00		1.40
b1	1.80		2.40
b2	2.80		3.40
c	0.40		0.75
D	19.80		21.20
D1		16.55	
D2		1.20	
E	15.20		16.00
E1		13.30	
E2		5.00	
E3		2.50	
e	5.20		5.70
L	13.90		20.70
L1	3.70		4.30
P	3.50		3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05		6.25
T		10.00	
U		6.20	

**Mechanical Dimensions TO-220AB**



Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	3.56	-	4.83
A1	0.51	-	1.40
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
c	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	9.65	-	10.67
e	-	2.54	-
e1	-	5.08	-
H1	5.84	-	6.86
L	12.70	-	14.73
L1	-	-	6.35
$\Phi P$	-	3.56	-
Q	2.54	-	3.43



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